

**TO-126 Plastic-Encapsulate Transistors****BD034** TRANSISTOR (PNP)**FEATURES**

Power dissipation

 P_{CM} : 1.25 W ($T_{amb}=25^{\circ}C$)

Collector current

 I_{CM} : -2.5 A

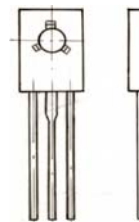
Collector-base voltage

 $V_{(BR)CBO}$: -110 V

Operating and storage junction temperature range

 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ **TO-126**

1. EMITTER
2. COLLECTOR
3. BASE



1 2 3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-110			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-100V, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-100mA$	100		560	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-1.5A$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-200mA$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5V, I_C=-500mA$			-1	V
Transition frequency	f_T	$V_{CE}=-1V, I_C=-250mA, f=1MHz$	3			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560

Typical Characteristics

BD034

